Dom ain free high eld superlattice transport

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The fundam ental condition for operating a superlattice (SL) as a B loch oscillator is a hom ogeneous electric eld alignment under large applied bias. This can be done by combining the nonlinear miniband transport channelwith a parallel shunt channel, connected through lateral transport. We report here about the rst realization of such a SL-shunt system . With the cleaved-edge-overgrow th (CEO) method we combine an undoped superlattice, which acts as the shunt, with a two-dimensional (2D) cleaved-edge surface superlattice channel. Our results con rm the long predicted current-voltage-characteristic (I-V) of a SL in a hom ogeneous DC electric eld. Excitation experiments in the GHz regime show that our shunt approach also works in the presence of an external AC electric eld. The device concept opens a clear path tow ands the realization of a solid state B loch oscillator.

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W hen Esakiand T su [1] proposed the fabrication of SL structures, they showed that these should exhibit a large region of negative-di erential conductance (NDC) due to the occurance of B loch oscillations [2], [3]. Since they found Bloch frequencies in the terahertz (THz) range, they suggested to use the SL as a solid state source in this regime. Sem iclassical calculations of the dynam ic conductivity of a SL by K titorov et al. [4] con m ed that the SL acts as a gain medium for all frequencies up to the Bloch frequency. About twenty years after these initial predictions, experiments, successfully revealing the formation of W annier-Stark ladders in biased SLs [5], and resolving B loch oscillations with the help of time dom ain spectroscopy [6], [7], [8], were perform ed. The excitation of a biased doped SL [9] also showed the theoretically predicted THz resonances in the photoconductivity of the SL sam ple. Theoretical ndings by W illenberg et al. [10] extend the K titorov results to a wide range of SL param eters and electric eld and tem perature regions. It was also possible to con m the theoretically predicted shape of the gain curve, by deriving the dynam ic conductivity from time domain spectoscopy results [11]. Recently, a direct observation of the crossover from loss to gain in a biased super-SL sturcture was successfully perform ed [12], m easuring the change in transm ission of a super-SL array, when bias was applied to the structure during the THz excitation.

N evertheless there exists no successful realization of an active solid state B loch oscillator up to now. The main obstacle in achieving such a device, is the instability of the electric eld in a region of NDC. This phenom enon is well known from the Gunn e ect [13]. Any uctuation in the electron density along the device, when it is biased in the NDC region, leads to a grow th of the uctuation and a redistribution of the electric eld in domains of small and large magnitudes. This destroys the equidistant Stark-ladder. In contrast, the hom ogeneous electric eld along the device is an essential requirement present in all theoretical calculations predicting gain in a

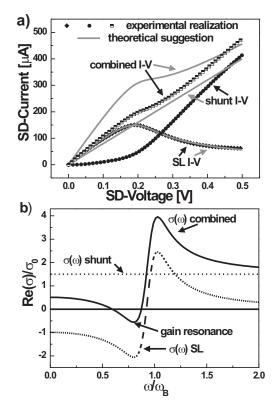


FIG.1: (a) Current-Voltage-characteristics of the shunt, the SL and the combined system suggested in [14] compared with the experim ental realization. Adding the shunt to the superlattice makes the overall conductivity positive and no instabilities occur. (b) If the realpart of the dynamic conductivity is smaller than the maximum gain at the resonance of the SL, then the combined system still exhibits gain close to the B loch frequency; adapted for our sam ples from [14].

SL structure. C onsequently, in order to realize an active B loch oscillator device one has to overcom e the problem of dom ain form ation. One such attempt is the super-SL structure employed in [12], in which individual SL sections are so short that full grown dom aims cannot be form ed. Under THz excitation this resulted in a hom ogeneous eld distribution across about 75 percent of the device. A nother approach tow ards avoiding the problem of instabilities was theoretically suggested by D aniel et al. [14]. The authors propose to combine the SL with a side shunt resistor which acts as an electric eld stabilizer in the static transport regim e. Their proposal is sum m arized in gure 1. The addition of the shunt can make the overall conductivity positive in the regim e of NDC. Num erical simulations show that the shunt can stabilize the electric eld distribution inside the SL up to a length scale of a few m icrons. In the dynam ic transport regim e one tries to arrange the structure in a way, that the real part of the dynam ic conductivity of the shunt increases the com bined conductivity, but is sm allenough such that the gain resonance of the SL becom es sm aller but is still present, as drawn in gure 1b.

In this letter we report the rst successful realization of a SL-shunt system that provides a hom ogeneous eld distribution across the SL.M olecular beam epitaxial grow th on the sidewall of an undoped SL employing the CEO method [15] allows us to combine the shunt and SL with atom ic precision and without problem s arising from poorly de ned or contam inated interfaces. Since our geom etry also results in direct control of the SL channel density, a complete separation of the two transport contributions is possible. Thus, for the rst time we can experimentally con m the long and often predicted I-V-characteristic of a superlattice under stable high eld conditions. The device gives entrance to a theoretically well studied, but experimentally so far inaccessible transport regime. The response of the SL-shunt systems to an external high-frequency (HF) eld con m s the form ation of a dom ain free eld distribution.

W e realize the SL-shunt system with the CEO method which, in the GaAs/AlGaAs system, allows the atom ically precise combination of two di erent growth steps (gure 2(a)). In a rst molecular-beam -epitaxy process we grow an undoped G aA s/A h:3G a0:7A s SL structure in between two n+-GaAs layers on a sem i-insulating [001] G aA s substrate. The undoped SL, whose transport properties can be modied by the doping concentration in the n+-layers, acts as the shunt in our structure. This layer sequence is then cleaved in situ along the [110] direction and is overgrown with a GaAs well, followed by an Al_{0:3}Ga_{0:7}As barrier and a n+ GaAs layer acting as a gate contact for the surface superlattice channel. The thickness of the cleaved edge well determ ines the bandstructure properties and m obilities, whereas the thickness of the gate barrier controls the ratio between source-drain-voltage (SDV) and gate bias. Two di erent SL system s with 25 periods of 15 nm length and 60 periods of 17 nm length were used for the samples. In both cases the SL wellwidth was 12 nm, while the barriers were 3 nm and 5 nm. For further reference we will call these 12/3 SL and 12/5 SL structures. The cleaved edge well thickness was varied between 0 nm and 20 nm. Those, with 5 nm well width and a gate barrier thicknesses of 100 nm and 500 nm, were chosen for the high-

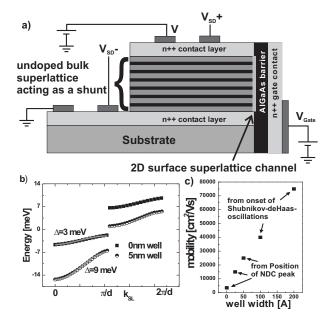


FIG.2: (a) Schem atic drawing of the sam ple structure. In (b) the theoretically calculated bandstructures along the surface SL are plotted for 0 nm and 5 nm cleaved-edge wellwidths, together with a sim ple cosine t. (c) An increase in the cleaved-edge well widths leads to a strong increase in the m obility of the surface SL.

eld transport studies. M agnetotransport m easurem ents revealed an adjustable 2D channel density between 0 and 10^{11} cm 2 for gate voltages between 0 and 7 V (500 6 nm barrier width). Figure 2 (b) shows the bandstructure of the 12/3 SL structure for cleaved edge well widths of 0 nm and 5 nm, calculated with the self-consistent Schrodinger-Poisson-Solvernextnano3 [16]. Our calculations show an increasing m in ibandw idth for thicker wells, but at the same time the in ection point moves towards the brillouin zone boundary and alm ost completely disappears for the 20 nm well. These ndings are in agreement with di erently based numerical calculations for equivalent structures [17]. A lthough the gaps to higher lying states appear rather sm all, the simulations show that these states belong to minibands form ed from excited subbands of the gate induced con nem ent potential. Since the spatial overlap between these subbands is vanishingly small, no signigicant tunneling between the lowest lying miniband and the excited ones is expected and also not observed in the experim ent. The miniband width of the 12/5 SL with the 5nm cleaved-edge well is 3.5 m eV

The I-V -characteristics of our devices depicted in gure 3 are measured at liquid helium temperature. An increasing voltage V is applied between the contact layers of the SL, while the current through the device and the voltage drop $V_{\rm SD}$ across the sample are measured as indicated in gure 2(a). In the inset of gure 3(a) a comparison between the I-V traces taken for zero applied gate bias and after the gate was mechanically removed shows, that

the gate control indeed allow sus to separate between the two transport channels. Since the shunt channel alone already represents transport through an undoped SL, the question of possible instabilities in this channel has to be addressed. The experim ental results show no abrupt instabilities up to Stark splittings, the energy associated with a voltage drop per SL period, of m ore than 25 m eV. The inset of gure 3 (b) shows the combined results for transport through both the shunt and the surface superlattice. The CEO method leads to a very exible sam ple design and allows the realization of di erent ratios between the magnitude of the two transport channels. W hile the shunt dom inates the shape of the 12/3 SL sample, the contributions are more equal for the 12/5 SL. After subtraction of the shunt transport from the I-V -characteristic of the combined system , the current carried by the surface superlattice is recovered and plotted in gure 3. The trace follows the long and offen predicted shape. For small electric elds, transport is essentially ohm ic. W ith increasing bias, the electron distribution starts to feel the non-linearity of the dispersion and the current saturates. Beyond this point electrons increasingly start to Bloch oscillate and the transport gradually decreases. In order to emphasize the importance of the shunt channel, gure 3 (a) also shows an I-Vcharacteristic of a sample with no such stabilizer. This was achieved by reduced doping in the n+ layers, for which a nite minimum voltage is needed to inject carriers into the SL. For this sample a typically observed current plateau due to eld inhom ogeneties is measured. The instability occurs at a source-drain- to gate voltage ratio of about 5 percent. Such high gate voltages are necessary to avoid a strong in uence of the sample bias on the gate induced con nem ent [18]. This fact is also stressed by the com parison of the 12/5 SL sam ples with 100 nm and 500 nm thick gate barriers also shown in gure 3(a). There, the current of the thin gate barrier sam ple drops quickly towards zero, which is largely caused by the fact that the increasing source-drain voltage reduces the con nem ent potential at the top contact and therefore causes an increasingly inhom ogeneous density and eld distribution along the surface SL. The 12/5 SL sample I-V is tted with the Esaki T su prediction Ι $\frac{1}{2}$, where the peak current was adjusted to 1+1 the experimental value and a series resistance of about 500 was included, which was independently con med by m agneto-resistance m easurem ents. An alm ost perfect agreem ent between experim ent and theory is found for this trace, but the sim ple theoretical result does not work equally well for other densities or the 12/3 SL sample. This is attributed to the fact, that a possible increase in the electronic tem perature for large electric elds has to be considered [19] and that the device and m easurem ent setup does not allow a direct determ ination of the voltage applied to the surface SL. In gure 3 (b) we plot the I-V-

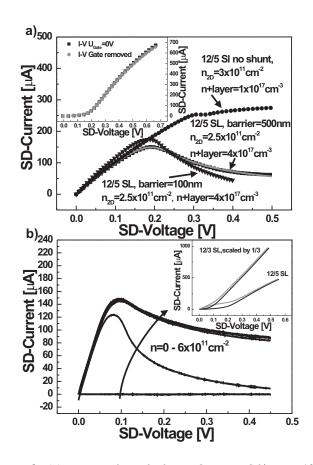


FIG.3: (a) Current through the surface SL of di erent 12/5 SL structures. The dots show a shunt free system which results in an inhom ogeneous electric eld distribution. The squares show the transport in a structure with a 500nm wide gate barrier. The resulting I-V-characteristic agrees excellently with the sem iclassical t (grey line). A thinner gate barrier (triangles) leads to quenching e ects for increasing SD-voltage. (b) Current through the surface SL of a 12/3SL sample for channel densities from 0 to 6 10^{11} cm² in steps of 10^{11} cm². The observed saturation in transport is theoretically expected.

characteristics of the 12/3 SL sample for densities up to $6 \ 10^{11}$ cm² in steps of 10^{11} cm². For higher densities a saturation of the overall transport is observed. This is theoretically expected from the lling of the 2D m iniband [18] and con rm sour theoretically calculated bandstructure. Sm all densities still show a more pronounced current drop due to the density reduction caused by the source-drain voltage increase.

From the current peak position scattering times of 350 fs and 500 fs, respectively, are extracted for the 12/5 SL and 12/3 SL structures, assuming $!_B = 1$ at the peak. Since the miniband width is smaller than the longitudinal optical phonon energy of 36 m eV in G aAs, prominently accoustic phonon scattering contributes to the inelastic scattering processes and is responsible for the overall transport along the surface SL.M oreover, as depicted in gure 2 (c) an increase in the cleaved-edge

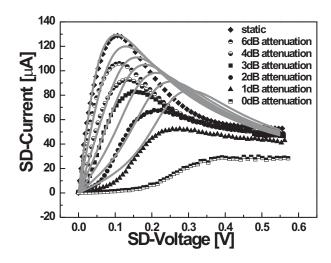


FIG. 4: The plot shows the DC transport characteristics of a 12/5 SL structure excited at 65 GHz for increasing input power. The grey lines are plotted from the evaluation of a sem iclassical theory. The sm aller experim ental values are attributed to an increased electron tem perature not considered in the theory.

wellwidth shows a strong increase of the mobility. Since the electronic system is thereby shifted away from the SL structure, this indicates strong elastic scattering by interface roughness, which is also observed in conventional SL transport. This elastic interface roughness scattering is responsible for the relatively short relaxation times measured and, since it strongly dom inates over the inelastic scattering, also for an observed large reduction of the peak current [19].

Finally we studied the response of our SL/shunt system to an externally applied HF eld F_{\perp} . The 12/5 SL sam plewasm ounted inside a wavequide which was tted with an a justable short at its end. It was then excited with a Gunn-oscillator operating at 65 GHz, mounted with an adjustable attenuator. During excitation the DC I-V-characteristics were measured. The results for various excitation powers P are plotted in gure 4. The device shows a strong response towards the HF excitation. The initially observed NDC peak is completely suppressed for large powers. A comparison with the sem iclassically expected response [20], which is plotted in 2 dB steps assum ing P F_{\perp}^{2} , show s qualitatively the same power dependence as our data. The fact that the measurem ents give system atically sm aller current values than those predicted by theory, is attributed to an increase in the effective electron tem perature, as a result of the expected long inelastic scattering tim es.

In summary we present the realization of a SL/shunt system, which allowed us to study static and dynamic transport in surface SLs with a homogeneous electric eld distribution, completely avoiding domain form ation. The samples reveal the long predicted stable I-V-characteristic of a SL. The large region of NDC due to electrons performing B loch oscillations is strikingly conm ed. Exciting the sam ples with GHz radiation also follows the sem iclassically expected behavior. A lthough the response is still quasistatic, due to the short relaxation times, the presented structure is an important rst step towards the realization of an acitve solid-state B boch oscillator. The remaining in uence of the gate structure on the measured traces can be further reduced by thicker gate barriers or completely avoided by *sw* itching to a modulation doped structure. Moreover, the better achievable mobilities in the 2D surface SL compared to 3D SL transport o er the advantage of a more pronounced gain maxim um below the B loch frequency.

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